

STANDARD RECOVERY DIODES

MAGN-A-pak™ Power Modules

Features

- High voltage
- Electrically isolated base plate
- 3000 V_{RMS} isolating voltage
- Industrial standard package
- Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL E78996 approved 

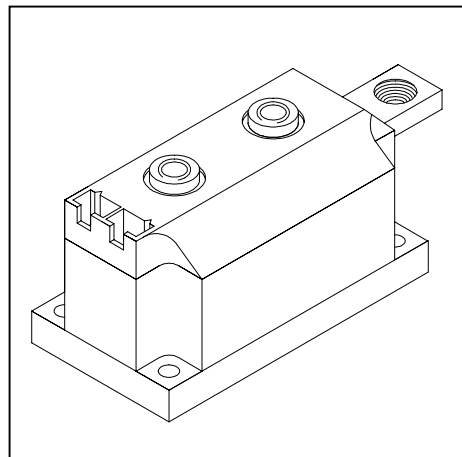
250A
270A
320A

Description

This new IRK series of MAGN-A-paks uses high voltage power diodes in two basic configurations. The semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges and the single diode module can be used in conjunction with the thyristor modules as a freewheel diode. These modules are intended for general purpose applications such as battery chargers, welders and plating equipment and where high voltage and high current are required (motor drives, etc.).

Major Ratings and Characteristics

Parameters	IRK.250..	IRK.270..	IRK.320..	Units
$I_{F(AV)}$	250	270	320	A
@ T_C	100	100	100	°C
$I_{F(RMS)}$	393	424	502	A
I_{FSM} @ 50Hz	7015	8920	10110	A
@ 60Hz	7345	9430	10580	A
I^2t @ 50Hz	246	398	511	KA ² s
@ 60Hz	225	363	466	KA ² s
$I^2\sqrt{t}$	2460	3980	5110	KA ² √s
V_{RRM}	Up to 2000	Up to 3000	Up to 2000	V
T_J	-40 to 150			°C



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , Maximum repetitive peak reverse voltage V	V_{RSM} , Maximum non-repetitive peak reverse voltage V	I_{RRM} Max @ 150°C mA
IRK.250-	04	400	500	50
IRK.270-	08	800	900	
IRK.320-	12	1200	1300	
	16	1600	1700	
	20	2000	2100	
IRK.320-	24	2400	2500	50
	30	3000	3100	

Forward Conduction

Parameters	IRK.250	IRK.270	IRK.320	Units	Conditions
$I_{F(AV)}$ Maximum average forward current @ Case temperature	250 100	270 100	320 100	A °C	180° conduction, half sine wave
$I_{F(RMS)}$ Maximum RMS forward current	393	424	502	A	as AC switch
I_{FSM} Maximum peak, one-cycle forward, non-repetitive surge current	7015 7345 5900 6180	8920 9340 7500 7850	10110 10580 8500 8900	A	$t = 10ms$ No voltage reappplied $t = 8.3ms$ 100% V_{RRM} reappplied $t = 10ms$ 100% V_{RRM} reappplied $t = 8.3ms$ 100% V_{RRM} reappplied Sinusoidal half wave, Initial $T_J = T_{Jmax}$
I^2t Maximum I^2t for fusing	246 225 174 159	398 363 281 257	511 466 361 330	KA ² s	$t = 10ms$ No voltage reappplied $t = 8.3ms$ 100% V_{RRM} reappplied $t = 10ms$ 100% V_{RRM} reappplied $t = 8.3ms$ 100% V_{RRM} reappplied
I^2/t Maximum I^2/t for fusing	2460	3980	5110	KA ² /s	$t = 0.1$ to $10ms$, no voltage reappplied
$V_{F(TO)1}$ Low level val. of threshold voltage	0.79	0.74	0.69	V	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}), T_J = T_{Jmax}$.
$V_{F(TO)2}$ High level val. of threshold voltage	0.92	0.87	0.86	V	$(I > \pi \times I_{F(AV)}), T_J = T_{Jmax}$.
r_{t1} Low level forward slope resistance	0.63	0.94	0.59	mΩ	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}), T_J = T_{Jmax}$.
r_{t2} High level forward slope resistance	0.49	0.81	0.44	mΩ	$(I > \pi \times I_{F(AV)}), T_J = T_{Jmax}$.
V_{FM} Maximum forward voltage drop	1.29	1.48	1.28	V	$I_{FM} = \pi \times I_{F(AV)}, T_J = T_{Jmax}, 180^\circ$ conduction $Av. power = V_{F(TO)} \times I_{F(AV)} + r_t \times (I_{F(RMS)})^2$

Blocking

Parameter	IRK.250/.270/.320	Units	Conditions
I_{RRM} Max. peak reverse leakage current	50	mA	$T_J = 150^\circ C$
V_{INS} RMS isolation voltage	3000	V	50Hz, circuit to base, all terminals shorted, $t = 1sec$

Thermal and Mechanical Specifications

Parameter		IRK.250 / .270 / .320			Units	Conditions
T _J	Max. junction operating temperature range	-40 to 150			°C	
T _{stg}	Max. storage temperature range	-40 to 150			°C	
R _{thJC}	Max. thermal resistance, junction to case	0.16	0.125	0.125	K/W	Per junction, DC operation
R _{thCS}	Max. thermal resistance, case to heatsink	0.035			K/W	Mounting surface flat, smooth and greased Per module
T	Mounting torque ±10%				Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound
	MAP to heatsink	4 to 6				
	busbar to MAP	8 to 10				
wt	Approximate weight	800 (30)			g (oz)	

ΔR Conduction (per Junction)

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Devices	Sinusoidal conduction @ T _J max.					Rectangular conduction @ T _J max.					Units
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
IRK.250-	0.009	0.010	0.014	0.020	0.032	0.007	0.011	0.015	0.021	0.033	K/W
IRK.270-	0.008	0.012	0.014	0.020	0.032	0.007	0.011	0.015	0.020	0.033	
IRK.320-	0.008	0.010	0.013	0.020	0.032	0.007	0.011	0.015	0.020	0.033	

Ordering Information Table

Device Code	IRK D 320 - 24 1 2 3 4				
1	-	Module type			
2	-	Circuit configuration			
3	-	Current rating: $I_{F(AV)} \times 10$ rounded			
4	-	Voltage code: Code $\times 100 = V_{RRM}$ (see Voltage Rating Table)			

Outline Table

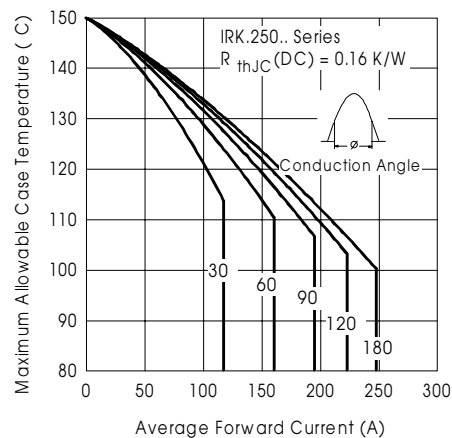
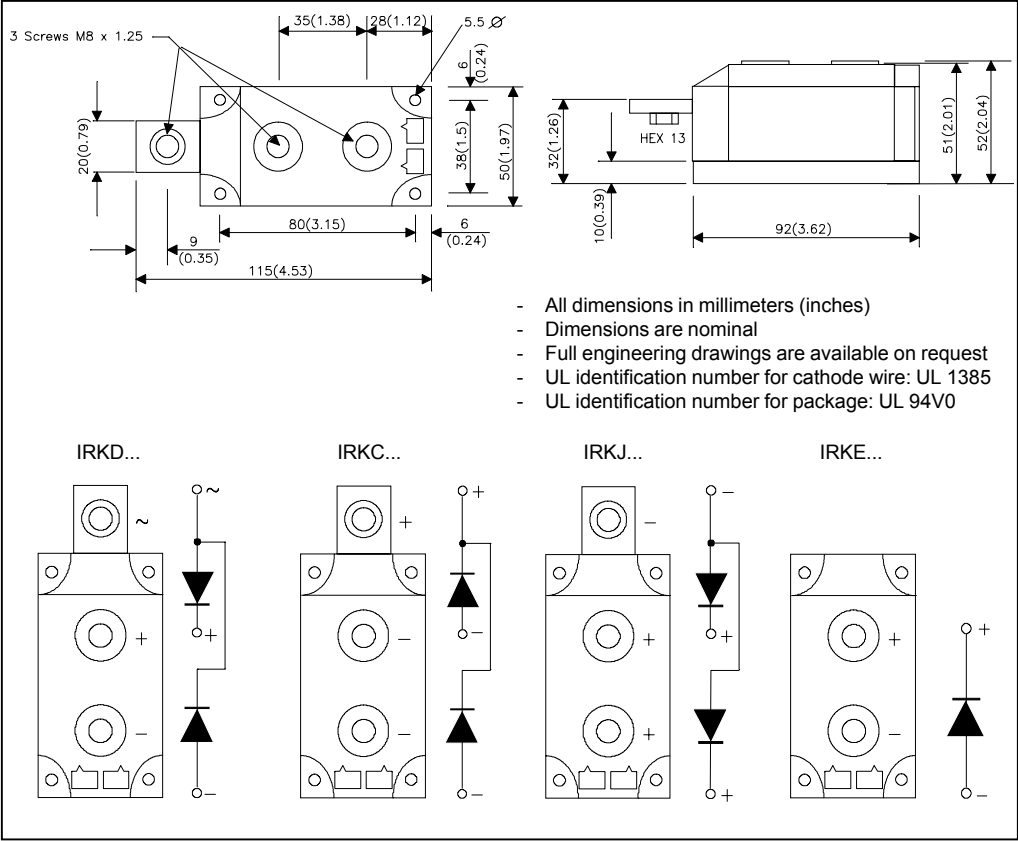


Fig. 1 - Current Ratings Characteristics

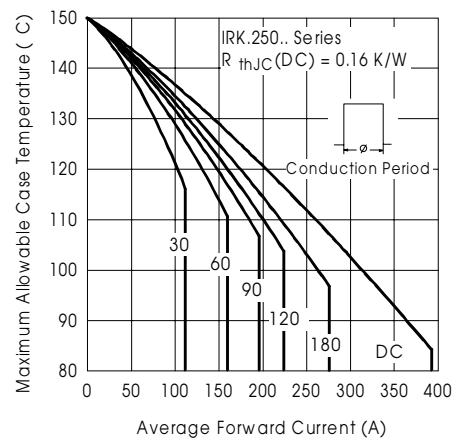


Fig. 2 - Current Ratings Characteristics

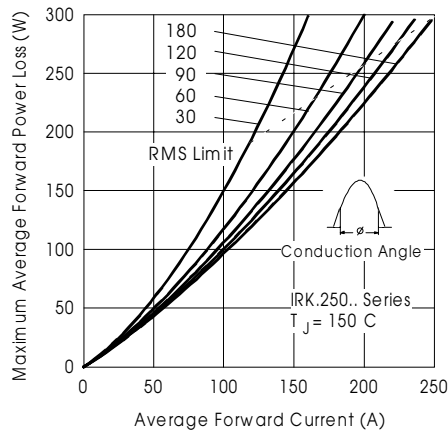


Fig. 3 - Forward Power Loss Characteristics

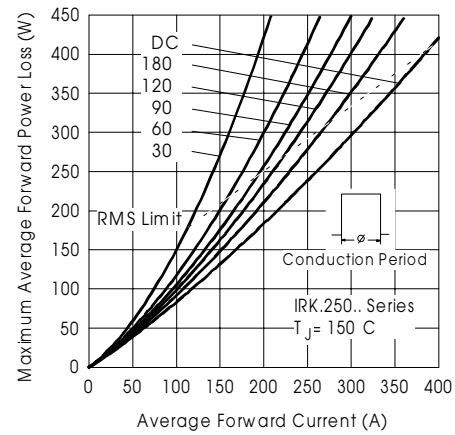


Fig. 4 - Forward Power Loss Characteristics

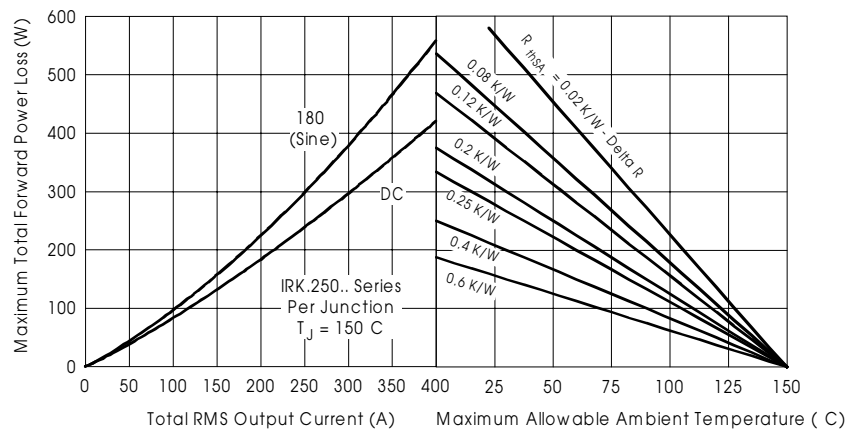


Fig. 5 - Forward Power Loss Characteristics

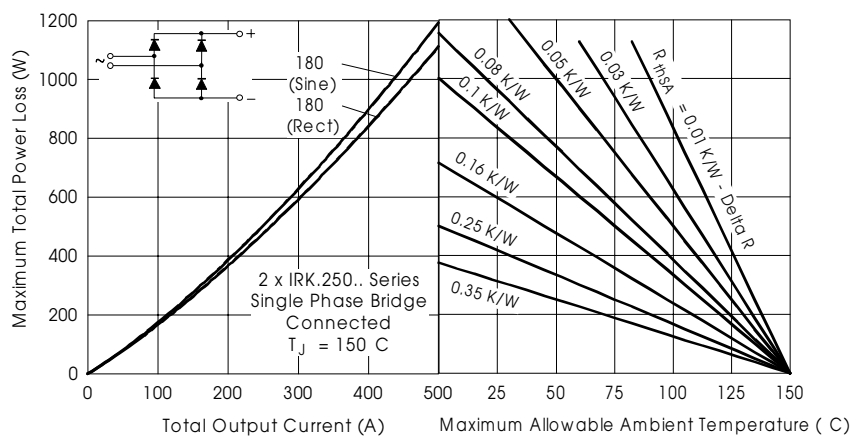


Fig. 6 - Forward Power Loss Characteristics

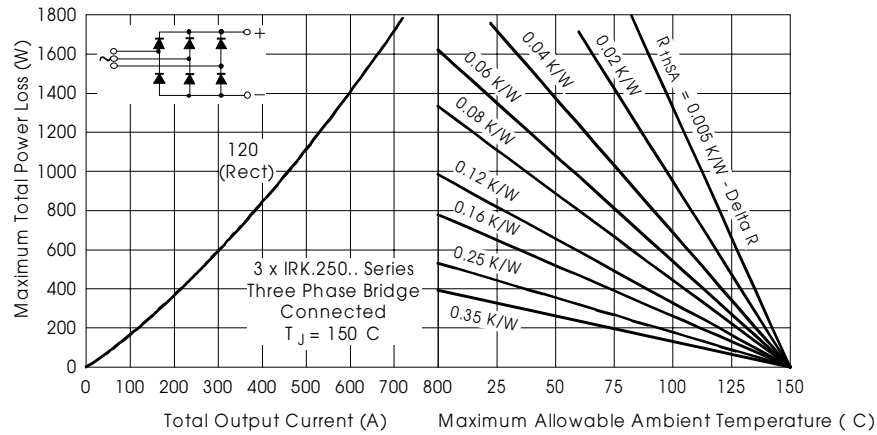


Fig. 7 - Forward Power Loss Characteristics

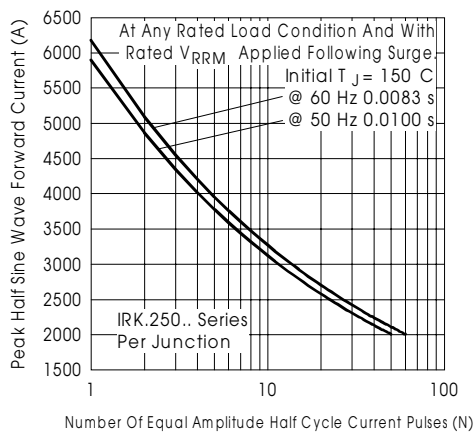


Fig. 8 - Maximum Non-Repetitive Surge Current

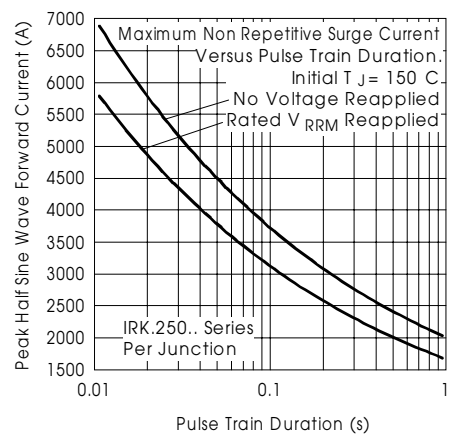


Fig. 9 - Maximum Non-Repetitive Surge Current

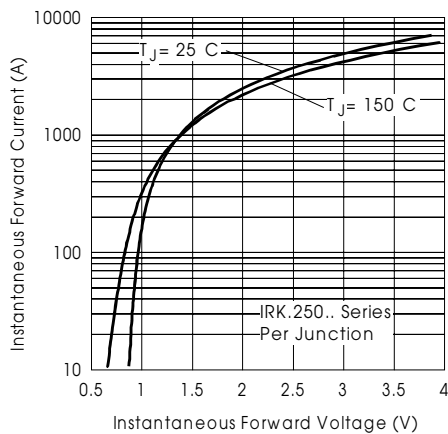


Fig. 10 - Forward Voltage Drop Characteristics

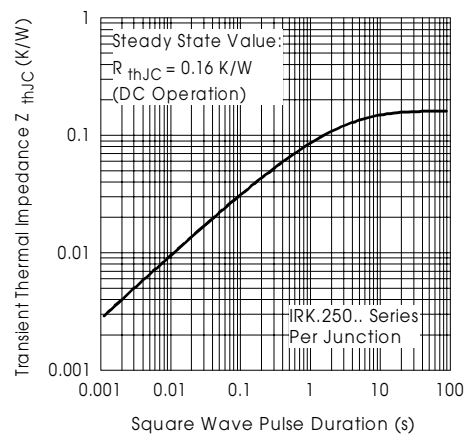


Fig. 11 - Thermal Impedance $Z_{\theta JC}$ Characteristics

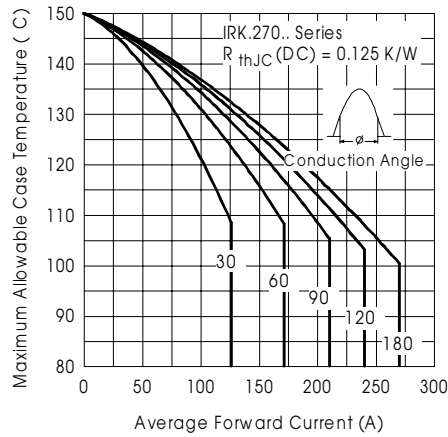


Fig. 12 - Current Ratings Characteristics

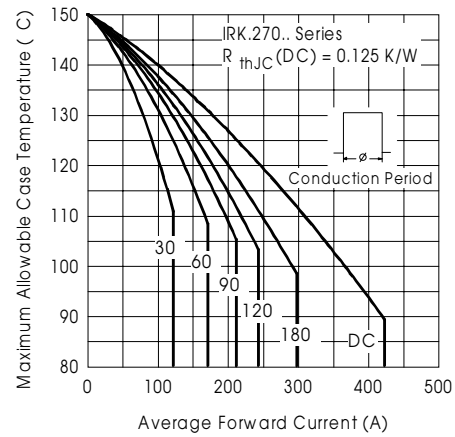


Fig. 13 - Current Ratings Characteristics

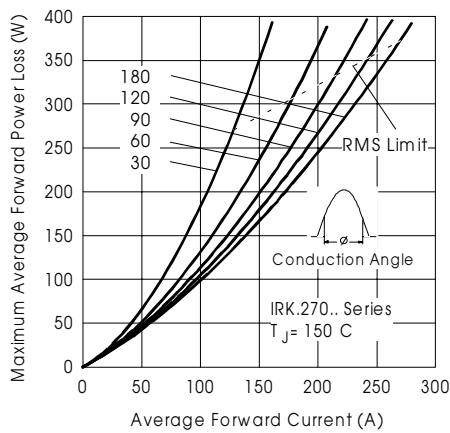


Fig. 14 - Forward Power Loss Characteristics

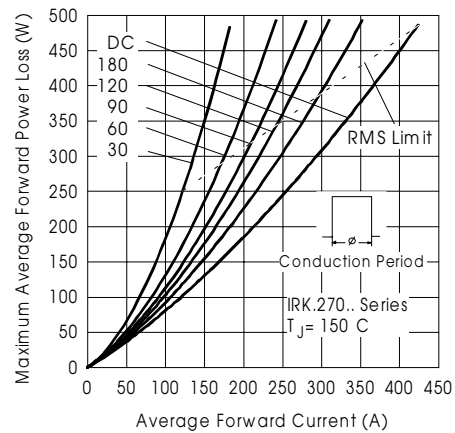


Fig. 15 - Forward Power Loss Characteristics

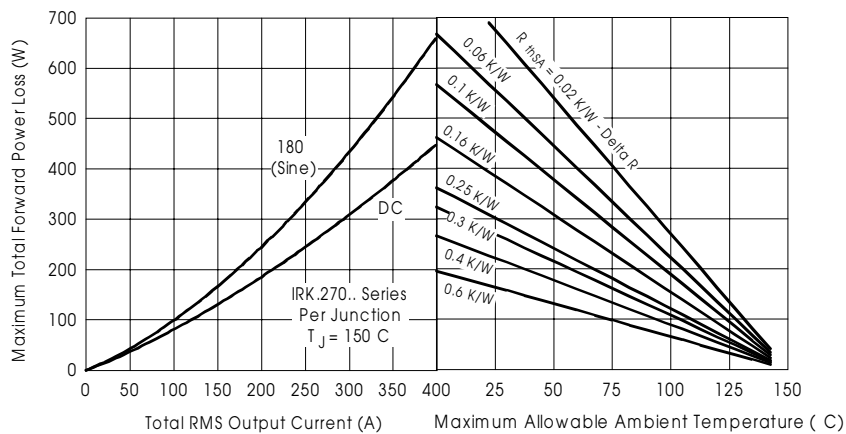


Fig. 16 - Forward Power Loss Characteristics

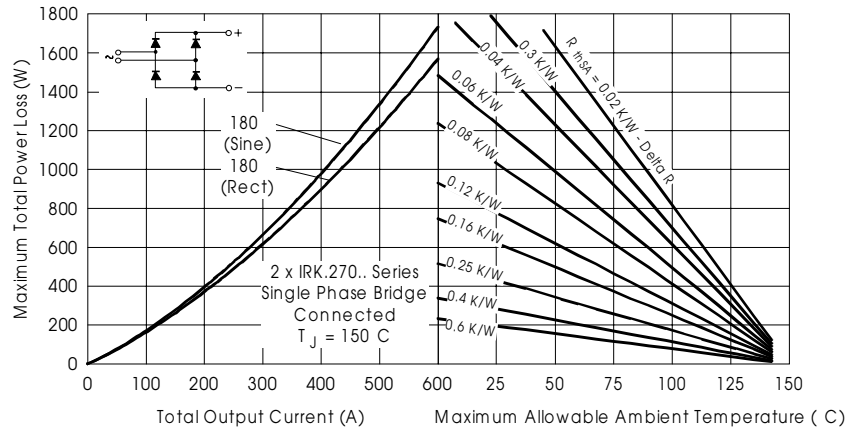


Fig. 17 - Forward Power Loss Characteristics

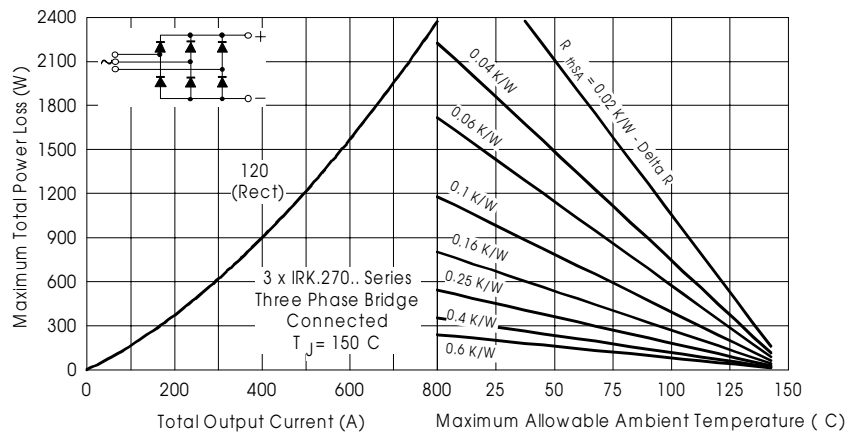


Fig. 18 - Forward Power Loss Characteristics

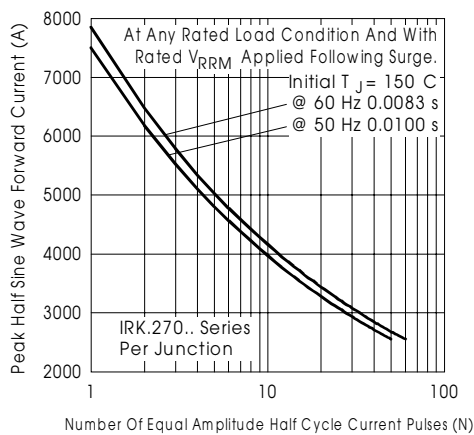


Fig. 19 - Maximum Non-Repetitive Surge Current

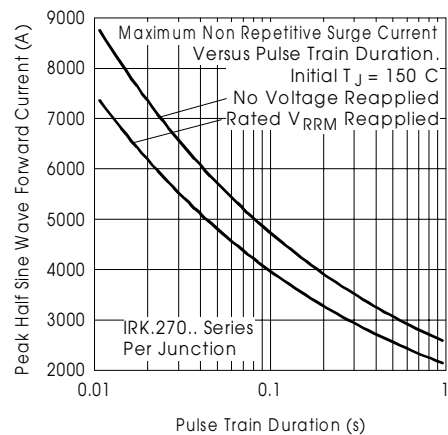


Fig. 20 - Maximum Non-Repetitive Surge Current

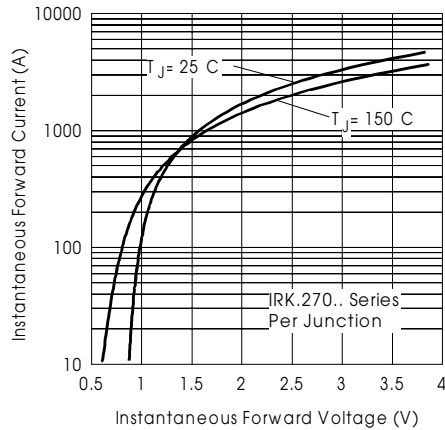


Fig. 21 - Forward Voltage Drop Characteristics

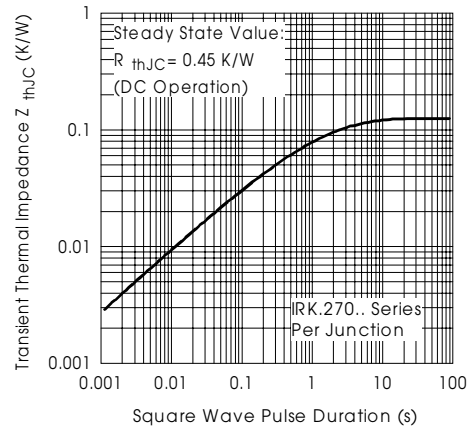


Fig. 22 - Thermal Impedance Z_{thJC} Characteristics

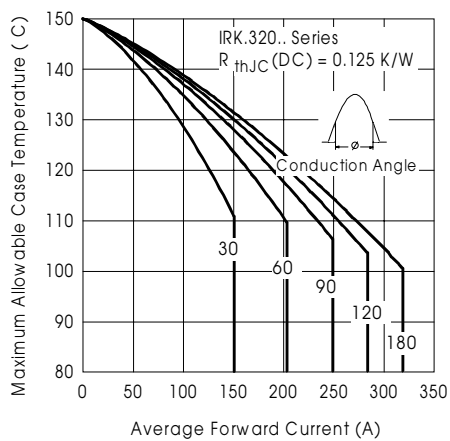


Fig. 23 - Current Ratings Characteristics

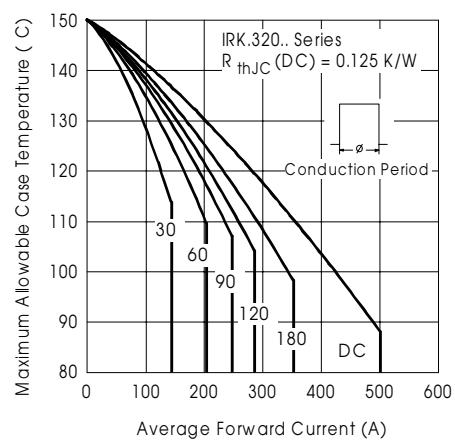


Fig. 24 - Current Ratings Characteristics

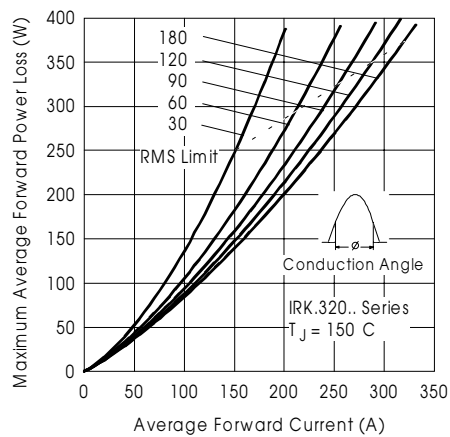


Fig. 25 - Forward Power Loss Characteristics

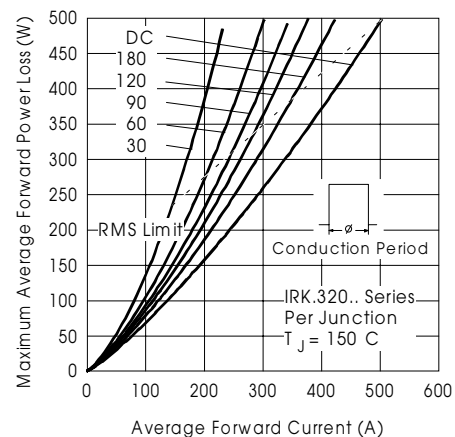


Fig. 26 - Forward Power Loss Characteristics

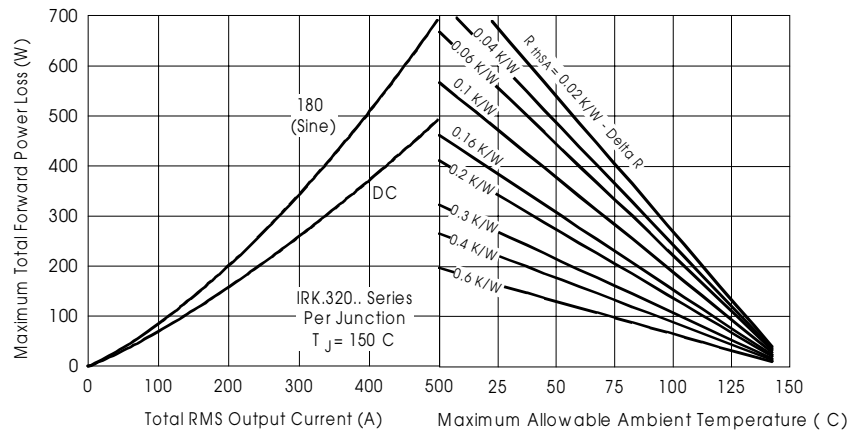


Fig. 27 - Forward Power Loss Characteristics

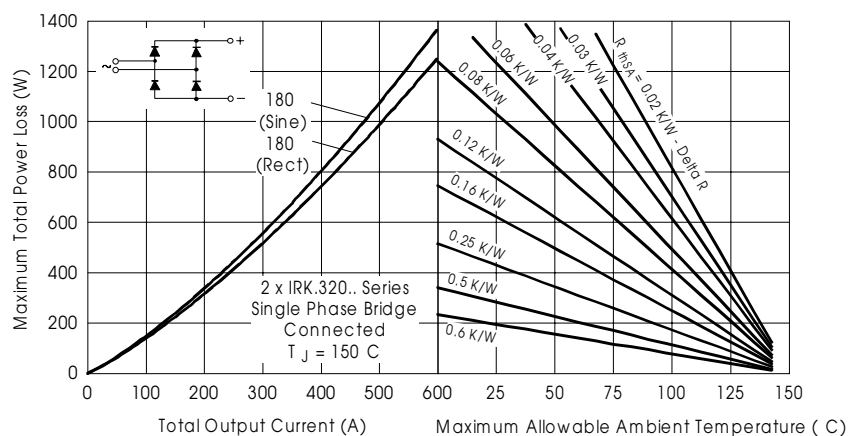


Fig. 28 - Forward Power Loss Characteristics

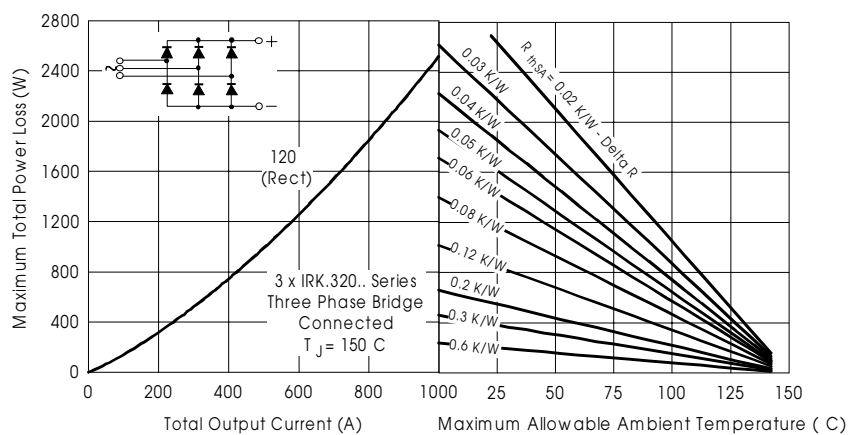


Fig. 29 - Forward Power Loss Characteristics

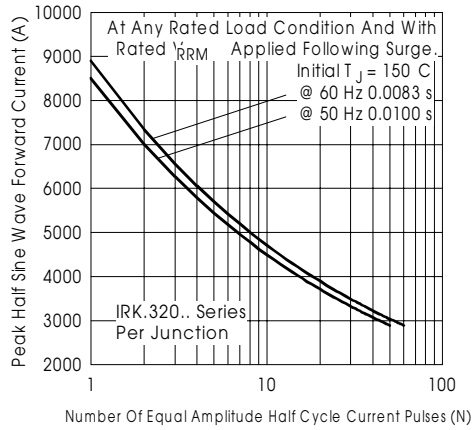


Fig. 30 - Maximum Non-Repetitive Surge Current

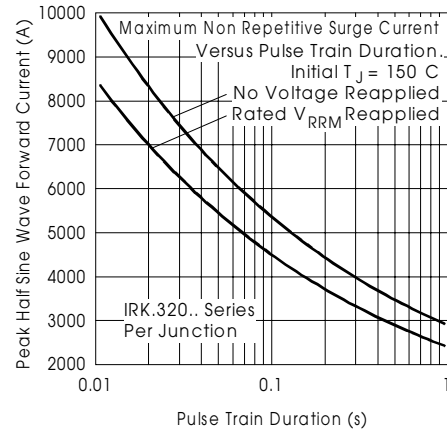


Fig. 31 - Maximum Non-Repetitive Surge Current

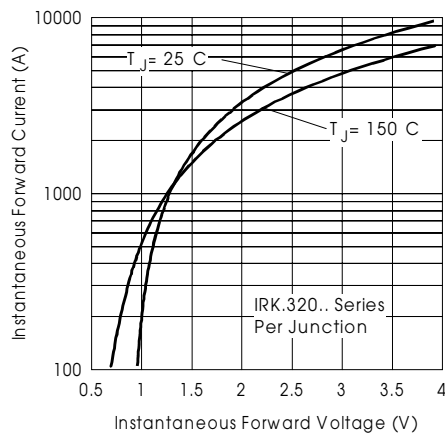


Fig. 32 - Forward Voltage Drop Characteristics

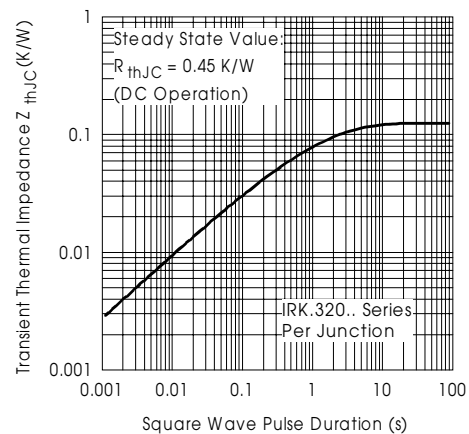


Fig. 33 - Thermal Impedance Z_{thJC} Characteristics

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7309
Visit us at www.irf.com for sales contact information. 05/02